



Form PTO/SB/0449

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**INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION**

(Use several sheets if necessary)

Applicant

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Group Art Unit 2811

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**U.S. PATENT DOCUMENTS**

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate

**FOREIGN PATENT DOCUMENTS**

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO

**OTHER DOCUMENTS**

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
OV	1.	Nagahama, S-i., et al. (2000). "High-Power and Long-Lifetime InGaN Multi-Quantum-Well Laser Diodes Grown on Low-Dislocation-Density GaN Substrates," <i>Jpn. J. Appl. Phys.</i> 39:L647-L650.
PW	2.	Tojyo, T. et al. (2002). "High-Power AlGaInN Laser Diodes with High Kink Level and Low Relative Intensity Noise," <i>Jpn. J. Appl. Phys.</i> 41:1829-1833.

EXAMINER:

DATE CONSIDERED:

7/17/06

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.